DISCRETE SEMICONDUCTORS

DATA SHEET

PMEGXX10BEA; PMEGXX10BEV

1 A very low V_F MEGA Schottky barrier rectifier

Product data sheet Supersedes data of 2004 Apr 02 2004 Jun 14



1 A very low V_F MEGA Schottky barrier rectifier

PMEGXX10BEA; PMEGXX10BEV

FEATURES

• Forward current: 1 A

• Reverse voltages: 20 V, 30 V, 40 V

· Very low forward voltage

· Ultra small and very small plastic SMD package

• Power dissipation comparable to SOT23.

APPLICATIONS

• High efficiency DC-to-DC conversion

· Voltage clamping

· Protection circuits

· Low voltage rectification

· Blocking diodes

• Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a very small SOD323 (SC-76) and ultra small SOT666 SMD plastic package.

MARKING

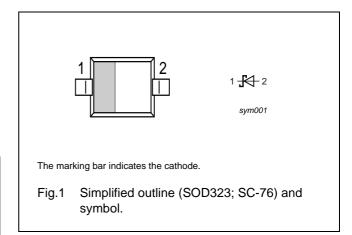
TYPE NUMBER	MARKING CODE
PMEG2010BEA	V1
PMEG3010BEA	V2
PMEG4010BEA	V3
PMEG2010BEV	G6
PMEG3010BEV	G5
PMEG4010BEV	G4

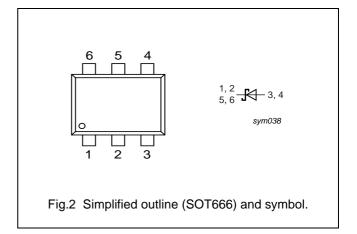
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
I _F	forward current	1	Α
V_R	reverse voltage	20; 30; 40	V

PINNING

PIN	DESCRIPTION		
PMEGXX10BEA (see Fig.1))		
1	cathode		
2	anode		
PMEGXX10BEV (see Fig.2)			
1, 2, 5, 6	cathode		
3, 4	anode		





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ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
ITPE NUMBER	NAME DESCRIPTION VE		VERSION
PMEGXX10BEA	plastic surface mounted package; 2 leads		SOD323
PMEGXX10BEV	plastic surface mounted package; 6 leads S0		SOT666

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage				
	PMEG2010BEA/PMEG2010BEV		_	20	V
	PMEG3010BEA/PMEG3010BEV		_	30	V
	PMEG4010BEA/PMEG4010BEV		_	40	V
I _F	continuous forward current	T _s ≤ 55 °C; note 1	_	1	Α
I _{FRM}	repetitive peak forward current	$t_p \le 1$ ms; $\delta \le 0.5$; note 2	_	3.5	Α
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms; square wave; note 2	_	10	А
T _j	junction temperature	note 3	_	150	°C
T _{amb}	operating ambient temperature	note 3	-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Notes

- 1. Refer to SOD323 (SC-76) and SOT666 standard mounting conditions.
- 2. Only valid if pins 3 and 4 are connected in parallel (SOT666 package).
- 3. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

1 A very low V_F MEGA Schottky barrier rectifier

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
PMEGXX10BEA (S	SOD323)			
R _{th(j-a)}	thermal resistance from junction to	in free air; notes 1 and 2	450	K/W
	ambient	in free air; notes 2 and 3	210	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point note 4		90	K/W
PMEGXX10BEV (S	OT666)			
R _{th(j-a)}	thermal resistance from junction to	in free air; notes 2 and 5	405	K/W
ambient		in free air; notes 2 and 6	215	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point	note 4	80	K/W

Notes

- 1. Refer to SOD323 (SC-76) standard mounting conditions.
- 2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.
- 3. Device mounted on an FR4 printed-circuit board with copper clad 10×10 mm.
- 4. Solder point of cathode tab.
- 5. Refer to SOT666 standard mounting conditions.
- 6. Only valid if pins 3 and 4 are connected in parallel (SOT666 package).

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	TER CONDITIONS PMEG2010BEA/PMEG2010BEV		PMEG3010BEA/ PMEG3010BEV		PMEG4010BEA/ PMEG4010BEV		UNIT	
			TYP.	MAX.	TYP.	MAX.	TYP.	MAX.	
V _F	forward voltage	I _F = 0.1 mA	90	130	90	130	95	130	mV
		I _F = 1 mA	150	190	150	200	155	210	mV
		I _F = 10 mA	210	240	215	250	220	270	mV
		I _F = 100 mA	280	330	285	340	295	350	mV
		I _F = 500 mA	355	390	380	430	420	470	mV
	$I_F = 1000 \text{ mA}$		420	500	450	560	540	640	mV
I _R	continuous	V _R = 10 V; note 1	15	40	12	30	7	20	μΑ
	reverse current	V _R = 20 V; note 1	40	200	_	_	_	_	μΑ
		V _R = 30 V; note 1	_	_	40	150	_	_	μΑ
		V _R = 40 V; note 1	_	_	_	_	30	100	μΑ
C _d	diode capacitance	V _R = 1 V; f = 1 MHz	66	80	55	70	43	50	pF

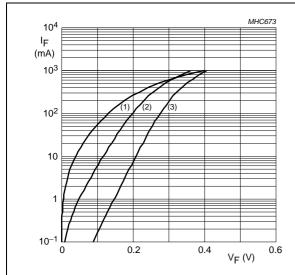
Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

1 A very low V_F MEGA Schottky barrier rectifier

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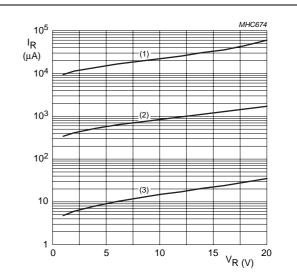
GRAPHICAL DATA



PMEG2010BEA/PMEG2010BEV

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

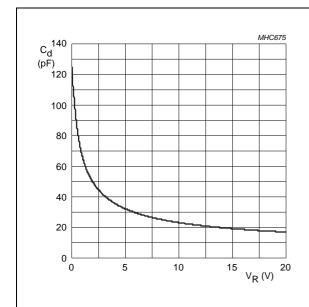
Fig.3 Forward current as a function of forward voltage; typical values.



PMEG2010BEA/PMEG2010BEV

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

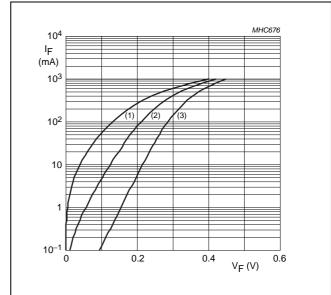
Fig.4 Reverse current as a function of reverse voltage; typical values.



PMEG2010BEA/PMEG2010BEV

 T_{amb} = 25 °C; f = 1 MHz.

Fig.5 Diode capacitance as a function of reverse voltage; typical values.



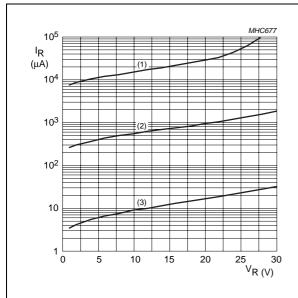
PMEG3010BEA/PMEG3010BEV

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.6 Forward current as a function of forward voltage; typical values.

1 A very low V_F MEGA Schottky barrier rectifier

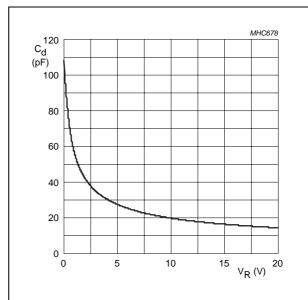
PMEGXX10BEA; PMEGXX10BEV



PMEG3010BEA/PMEG3010BEV

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

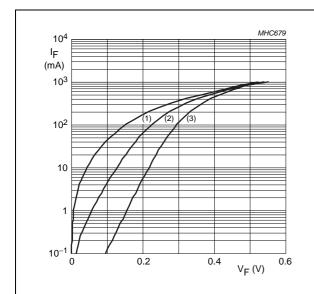
Fig.7 Reverse current as a function of reverse voltage; typical values.



PMEG3010BEA/PMEG3010BEV

 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz.$

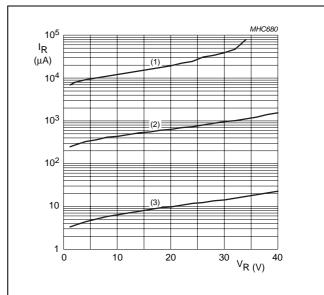
Fig.8 Diode capacitance as a function of reverse voltage; typical values.



PMEG4010BEA/PMEG4010BEV

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.9 Forward current as a function of forward voltage; typical values.



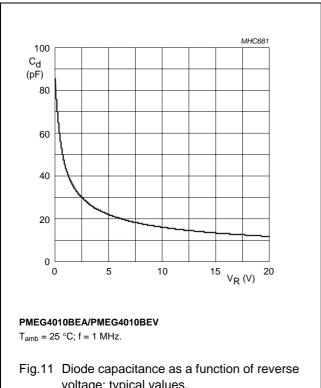
PMEG4010BEA/PMEG4010BEV

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) T_{amb} = 85 °C.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.10 Reverse current as a function of reverse voltage; typical values.

1 A very low V_F MEGA Schottky barrier rectifier

PMEGXX10BEA; PMEGXX10BEV



voltage; typical values.

7 2004 Jun 14

1 A very low V_F MEGA Schottky barrier rectifier

PMEGXX10BEA; PMEGXX10BEV

PACKAGE OUTLINES

SOD323 Plastic surface-mounted package; 2 leads A = v M A Q detail X 2 mm **DIMENSIONS** (mm are the original dimensions) A₁ max L_p UNIT bp H_D 0.25 0.10 0.40 0.45 0.25 mm 0.05 0.2 0.8 0.25

Note

1. The marking bar indicates the cathode

OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOD323			SC-76			-03-12-17- 06-03-16

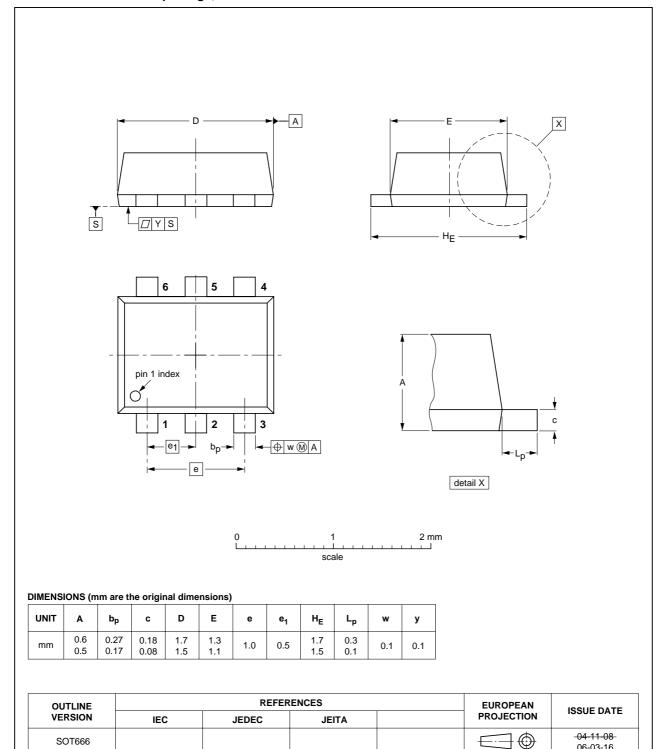
1 A very low V_F MEGA Schottky barrier rectifier

PMEGXX10BEA; PMEGXX10BEV

Plastic surface-mounted package; 6 leads

SOT666

06-03-16



2004 Jun 14 9

1 A very low V_F MEGA Schottky barrier rectifier

PMEGXX10BEA; PMEGXX10BEV

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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